Am93L415/Am93L425

1024 x 1 Bit TTL Bipolar IMOX™ RAM

DISTINCTIVE CHARACTERISTICS

- Fully decoded 1024-word x 1-bit RAMs
- 93L415A/425A has a 35 ns maximum access time, 65 mA I_{CC}
- Internal ECL circuitry for optimum speed/power performance over voltage and temperature
- Output preconditioned during write to eliminate write recovery glitch
- Available with three-state outputs (Am93L425 series) or with open-collector outputs (Am93L415 series)
- Plug-in replacement for Fairchild 93L415A/415 and 93L425A/425, and Intel 2115/2125 series

GENERAL DESCRIPTION

The Am93L415 and Am93L425 are fully decoded 1024 x 1 RAMs built with Schottky diode clamped transistors in conjunction with internal ECL circuitry. They are ideal for use in high-speed control and buffer memory applications. Easy memory expansion is provided by an active LOW chip select input (CS) and either open-collector (93L415) or three-state (93L425) output. Chip selection for large memory systems can be controlled by active LOW output decoders such as the Am74S138.

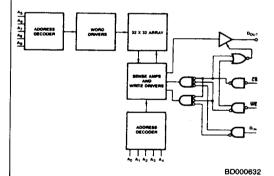
An active LOW write line (\overline{WE}) controls the writing/reading operation of the memory. When the chip select (\overline{CS}) and write lines (\overline{WE}) are LOW, the information on the data input

(D_{IN}) is written into the addressed memory word and the output circuitry preconditioned so that true data is present at the output when the write cycle is complete. This preconditioning operation insures minimum write recovery times by eliminating the "write recovery glitch."

Reading is performed with the chip select line LOW and the write line HIGH. The information stored in the addressed word is read out on the noninverting output (D_{OUT}).

During the reading and writing operation or any time the chip select line is HIGH, the output of the memory goes to an inactive high-impedance state.

BLOCK DIAGRAM



MODE SELECT TABLE

			Output	
CS			DOUT	Mode
н	×	×	*Hi-Z	Not Selected
L	L	L	*Hi-Z	Write "0"
L	L	Н	*Hi-Z	Write "1"
L	н	х	Selected Data	Read

H = HIGH L = LOW X = Don't Care

*Hi-Z implies outputs are disabled or off. This condition is defined as a high-impedance state for the Am93L425 series and as an output high level for the Am93L415 series.

PRODUCT SELECTOR GUIDE

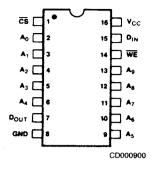
Access Time	35 ns	40 ns	ns 45 ns		60 ns
Temperature Range	С	М	С	М	С
Open-Collector	Am93L415SA	Am93L415SA	Am93L415A	Am93L415A	Am93L415
Three-State	Am93L425SA	Am93L425SA	Am93L425A	Am93L425A	Am93L425

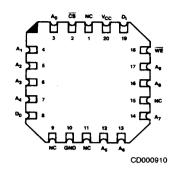
IMOX is a trademark of Advanced Micro Devices, Inc.

Publication # Rev. Amendment
05850 C /0
Issue Date: May 1986

3-143

CONNECTION DIAGRAMS Top View



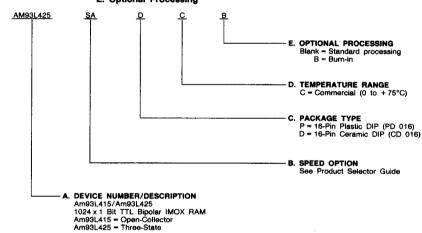


ORDERING INFORMATION (Cont'd.)

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: **A. Device Number**

- B. Speed Option (if applicable)
- C. Package Type
 D. Temperature Range
- E. Optional Processing



Valid Combinations AM93L415SA AM93L425SA AM93L415A PC, PCB, AM93L425A AM93L425A DC, DCB AM93L415 AM93L425

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

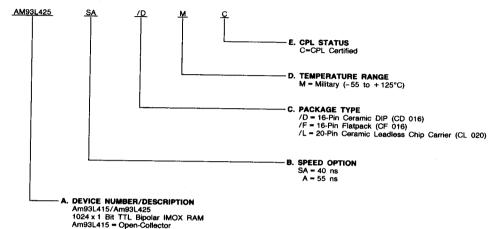
ORDERING INFORMATION

CPL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. CPL (Controlled Products List) products are processed in accordance with MIL-STD-883C, but are inherently non-compliant because of package, solderability, or surface treatment exceptions to those specifications. The order number (Valid Combination) for APL products is formed by a combination of: A. Device Number

- B. Speed Option (if applicable)
- C. Package Type
- D. Temperature Range





Valid Combinations AM93L425SA /DMC, AM93L415SA /FMC,

AM93L415A

/LMC

Am93L425 = Three-State

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature	65 to +150°C
Ambient Temperature with	
Power Applied	55 to +125°C
Supply Voltage	0.5 V to +7.0 V
DC Voltage Applied to Outputs	-0.5 V to +V _{CC} Max.
DC Input Voltage	0.5 V to +5.5 V
DC Input Current	30 mA to +5 mA

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device

reliability.

OPERATING RANGES (Note 6)

Commercial (C) Devices	
Temperature	0 to +75°C
Supply Voltage	
Military (M) Devices	
Temperature	55 to +125°C
Supply Voltage	+ 4.5 V to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified*

Parameter Symbol	Parameter Description	Test Co	Min.	Typ. (Note 1)	Max.	Units	
V _{OH} (Note 2)	Output HIGH Voltage	V_{CC} = Min. V_{IN} = V_{IH} or V_{IL} I_{OH} = -5.2 mA		2.4	3.4		Volts
VOL	Output LOW Voltage	V _{CC} = Min., V _{IN} = V _{IH} or V _{IL}	I _{OL} = 16 mA		0.33	0.45	Volts
ViH	Input HIGH Level (Note 3)	Guaranteed input logical HI	Guaranteed input logical HIGH voltage for all inputs				Volts
ViL	Input LOW Level (Note 3)	Guaranteed input logical LO			0.8	Volts	
hL.	Input LOW Current	V _{CC} = Max., V _{IN} = 0.40 V		-90	-300	μΑ	
hн	Input HIGH Current	V _{CC} = Max., V _{IN} = 4.5 V		1	40	μΑ	
ISC (Note 2)	Output Short Circuit Current	V _{CC} = Max., V _{OUT} = 0.0 V (Note 5)		-20	-50	-100	mA
lcc	Power Supply Current	All inputs = GND Commercial V _{CC} = Max. Military				65	mA
'CC	Tower Supply Current					75	
V _{CL}	Input Clamp Voltage	V _{CC} = Min., I _{IN} = -10 mA			-0.850	-1.5	Volts
		CS = VIH or WE = VII	Am93L415 Series Only		0	100	
loev	Output Leakage Current	V _{OUT} = 2.4 V	Am93L425 Series Only		0	50	μΑ
ICEX	Output Leakage Cullent	CS = VIH or WE = VIL VOUT = 0.5 V, VCC = Max.	Am93L425 Series Only	-50	0		,,,,
CIN	Input Pin Capacitance	See Note 4			8		рF
Сопт	Output Pin Capacitance	See Note 4			10		pF

Notes: 1. Typical limits are at VCC = 5.0 V and TA = 25°C.

2. This applies only to devices with three-state output. (Am93L425 series)

3. These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise.

Do not attempt to test these values without suitable equipment.

4. Input and output capacitance measured on a sample basis using pulse technique.

Duration of the short circuit should not be more than one second.
 Operating specification with adequate time for temperature stabilization and transverse air flow exceeding 400 linear feet per minute. Conformance testing performed instantaneously where T_A = T_C = T_J.

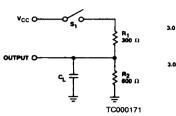
 $\theta_{\rm JA} \approx 60^{\circ} \text{fw}$ (with moving air) for Ceramic DIP. $\theta_{\rm JC} \approx 10-17^{\circ} \text{fw}$ for Flatpack.

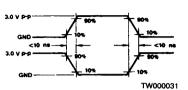
*See the last page of this spec for Group A Subgroup Testing information.

SWITCHING TEST **CIRCUIT**

SWITCHING TEST WAVEFORM

KEY TO SWITCHING WAVEFORMS





WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H
XXXX	DON'T CARE; ANY CHANGE PERMITTED	CHANGING; STATE UNKNOWN
}} ({{	DOES NOT	CENTER LINE IS HIGH IMPEDANCE "OFF" STATE
		KS000010

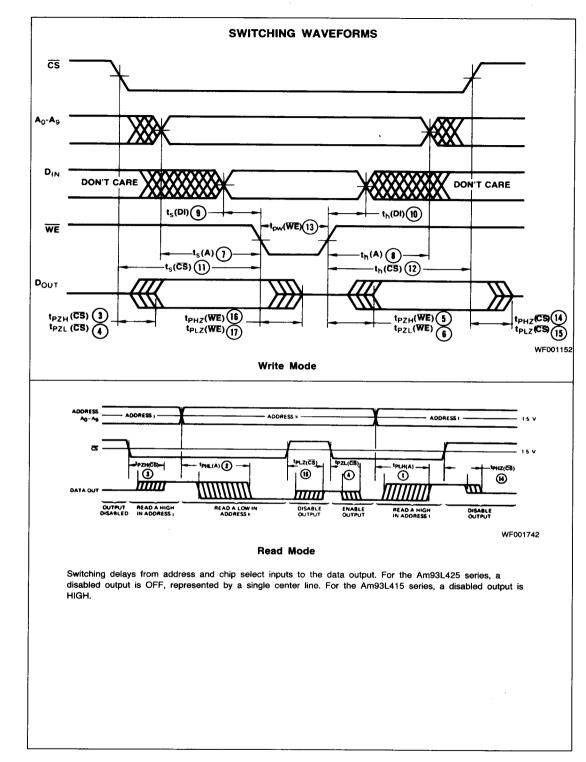
SWITCHING CHARACTERISTICS over operating range unless otherwise specified*

						Am93L415A-Am93L425A				Am93L415/ Am93L425			
	l_		COM'L		MIL		COM'L		MIL		COM'L		
No.	Parameter Symbol	Parameter Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
1	t _{PLH} (A)	Delay from Address to Output	1	35		40		45		55		60	ns
2	t _{PHL} (A)	(Note 1)				10		~~]	33		00	115
3	t _{PZH} (CS)	Delay from Chip Select to Active		25		40		30		45		40	
4	tpZL(CS)	Output (Notes 2 and 3)		23		**	Ĭ	30		45		40	ns
5	t _{PZH} (WE)	Delay from Write Enable to Active Output		20		30		25		35		45	
6	tpZL(WE)	(Write Recovery) (Note 2 and 3)		-		"	l	23		33		45	ns
7	t _S (A)	Setup Time Address (Prior to Initiation of Write)	5		5		5		5		5		ns
8	t _h (A)	Hold Time Address (After Termination of Write)	5		5		5		5		5		ns
9	t _B (DI)	Setup Time Data Input (Prior to Initiation of Write)	0		5		0		5		5		ns
10	t _h (DI)	Hold Time Data Input (After Termination of Write)	5		5		5		5		5		ns
11	t _s (ĈŜ)	Setup Time Chip Select (Prior to Initiation of Write)	5		5		5		5		5		ns
12	t _h (CS)	Hold Time Chip Select (After Termination of Write)	5		5		5		5		5		ns
13	t _{pw} (₩E)	Write Enable Pulse Width to Insure Write	25		30		30		45	-	45		ns
14	t _{PHZ} (CS)	Delay from Chip Select to Inactive		30		35		05					
15	tpLZ(CS)	Output (Hi-Z) (Notes 2 and 3)		30		35		35		40		40	ns
16	t _{PHZ} (WE)	Delay from Write Enable to Inactive		20		25							
17	tpLZ(WE)	Output (Hi-Z) (Notes 2 and 3)		30		35		35		40	İ	45	ns

- Notes: 1. tp_H(A) and tpHL(A) are tested with S₁ closed and C_L = 30 pF with both input and output timing referenced to 1.5 V.

 2. For open-collector devices (93L415 series), delays for WE and CS to either an active or inactive output are measured with S₁
 - closed and CL = 30 pF; both input and output timing referenced to 1.5 V.
 - 3. For three-state output devices (931.425 series), delays for tp_{ZH} and tp_{ZL} are measured with C_L = 30 pF, S₁ open and S₁ closed, respectively. Both input and output timing are referenced to 1.5 V. Delays for tp_{HZ} with S₁ open and tp_{LZ} with S₁ closed and C_L ≤ 5 pF are measured between the 1.5 V level on the input and the V_{OH} −0.5 V and V_{OL} +0.5 V level on the output, respectively.

^{*}See the last page of this spec for Group A Subgroup Testing information.



GROUP A SUBGROUP TESTING

DC CHARACTERISTICS

Parameter Symbol	Subgroups
V _{OH}	1, 2, 3
V _{OL}	1, 2, 3
V _{IH}	1, 2, 3
VIL	1, 2, 3
կլ	1, 2, 3
ΉΗ	1, 2, 3
Isc	1, 2, 3
lcc	1, 2, 3
V _{CL}	1, 2, 3
ICEX	1, 2, 3

SWITCHING CHARACTERISTICS

No.	Parameter Symbol	Subgroups	No.	Parameter Symbol	Subgroups
1	t _{PLH} (A)	9, 10, 11	10	th(DI)	9, 10, 11
2	t _{PHL} (A)	9, 10, 11	11	t _s (CS)	9, 10, 11
3	t _{PZH} (CS)	9, 10, 11	12	th(CS)	9, 10, 11
4	t _{PZL} (CS)	9, 10, 11	13	t _{pw} (WE)	9, 10, 11
5	t _{PZH} (WE)	9, 10, 11	14	t _{PHZ} (CS)	9, 10, 11
6	t _{PZL} (WE)	9, 10, 11	15	t _{PLZ} (CS)	9, 10, 11
7	t _s (A)	9, 10, 11	16	t _{PLZ} (WE)	9, 10, 11
8	t _h (A)	9, 10, 11	17	t _{PHZ} (WE)	9, 10, 11
9	t _s (DI)	9, 10, 11			

MILITARY BURN-IN

Military burn-in is in accordance with the current revision of MIL-STD-883, Test Method 1015, Conditions A through E. Test conditions are selected at AMD's option.